

N-Channel Enhancement Mode Power MOSFET

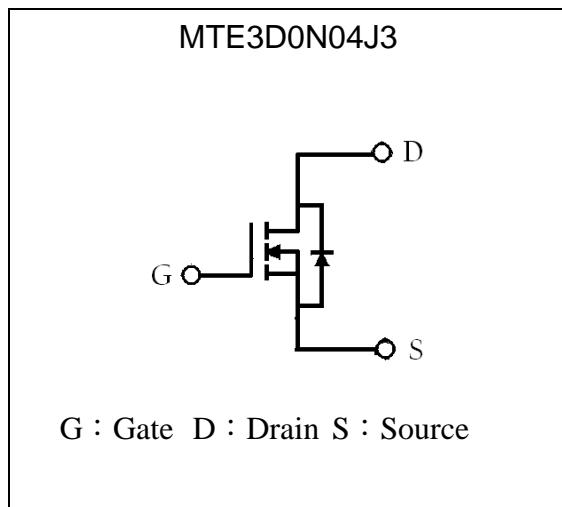
MTE3D0N04J3

BV_{DSS}	40V
I_D@V_{GS}=10V, T_C=25°C	96.6A(silicon limit)
I_D@V_{GS}=10V, T_C=25°C	56A(package limit)
R_{DS(ON)}@V_{GS}=10V, I_D=20A	2.8 mΩ (typ)

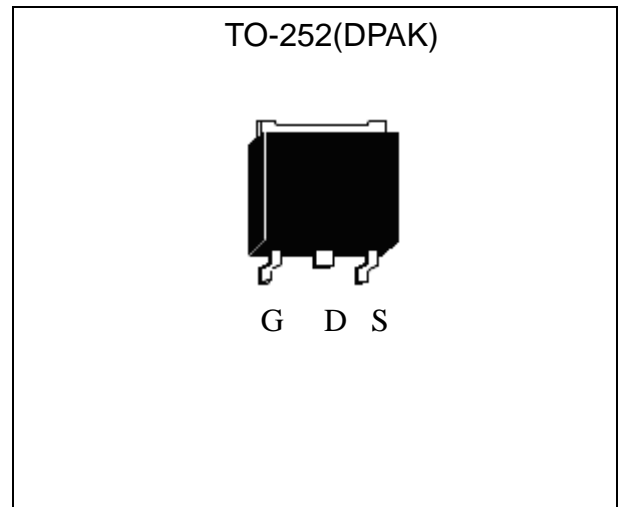
Features

- Low On Resistance
- Simple Drive Requirement
- Low Gate Charge
- Fast Switching Characteristic
- Pb-free lead plating and halogen-free package

Symbol

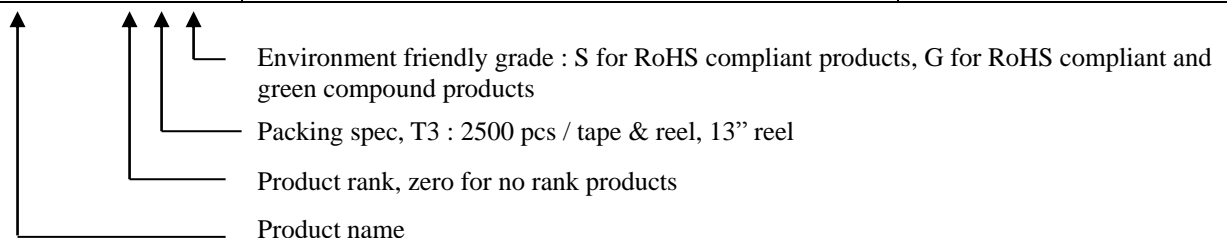


Outline



Ordering Information

Device	Package	Shipping
MTE3D0N04J3-0-T3-G	TO-252 (Pb-free lead plating and halogen-free package)	2500 pcs / tape& reel



**Absolute Maximum Ratings** ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit	
Drain-Source Voltage (Note 1)	V_{DS}	40	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current @ $T_C=25^\circ\text{C}$, $V_{GS}=10\text{V}$ (silicon limit) (Note 5)	I_D	96.6	A	
Continuous Drain Current @ $T_C=100^\circ\text{C}$, $V_{GS}=10\text{V}$ (silicon limit) (Note 5)		68.3		
Continuous Drain Current @ $T_C=25^\circ\text{C}$, $V_{GS}=10\text{V}$ (package limit) (Note 5)		56		
Continuous Drain Current @ $T_A=25^\circ\text{C}$, $V_{GS}=10\text{V}$ (Note 2)	I_{DSM}	18.4		
Continuous Drain Current @ $T_A=70^\circ\text{C}$, $V_{GS}=10\text{V}$ (Note 2)		14.7		
Pulsed Drain Current @ $V_{GS}=10\text{V}$ (Note 3)	I_{DM}	386		
Avalanche Current @ $L=0.1\text{mH}$	I_{AS}	90		
Single Pulse Avalanche Energy @ $L=1\text{mH}$, $I_D=40\text{A}$, $V_{DD}=25\text{V}$ (Note 4)	E_{AS}	800	mJ	
Power Dissipation	P_D	$T_C=25^\circ\text{C}$ (Note 1)	100	W
		$T_C=100^\circ\text{C}$ (Note 1)	50	
	P_{DSM}	$T_A=25^\circ\text{C}$ (Note 2)	2.5	
		$T_A=70^\circ\text{C}$ (Note 2)	1.6	
Operating Junction and Storage Temperature	T_j, T_{stg}	-55~+175	$^\circ\text{C}$	

Stress exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Thermal Data

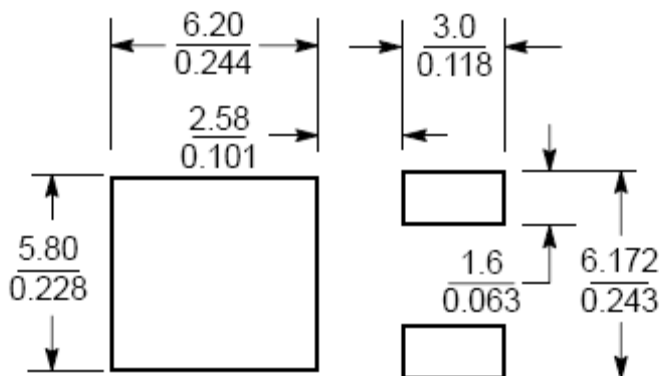
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{\theta JC}$	1.5	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-ambient, max (Note 2)	$R_{\theta JA}$	50	

- Note :
- The power dissipation P_D is based on $T_{J(MAX)}=175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
 - The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with $T_A=25^\circ\text{C}$. The power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C .
 - Pulse width limited by junction temperature $T_{J(MAX)}=175^\circ\text{C}$. Ratings are based on low frequency and low duty cycles to keep initial $T_J=25^\circ\text{C}$.
 - 100% tested by conditions of $L=0.1\text{mH}$, $V_{GS}=10\text{V}$, $I_{AS}=50\text{A}$, $V_{DD}=25\text{V}$
 - Calculated continuous current based on maximum allowable junction temperature. Guaranteed by design, not subject to 100% production test. Current is limited to 56A by source bond technology.

Characteristics (T_j=25°C, unless otherwise specified)

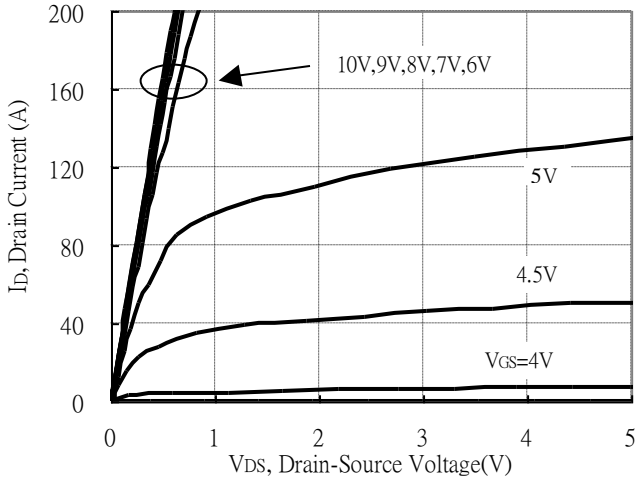
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	40	-	-	V	V _{GS} =0V, I _D =250μA
ΔBV _{DSS} /ΔT _j	-	0.03	-	V/°C	Reference to 25°C, I _D =250μA
V _{GS(th)}	2	-	4	V	V _{DS} = V _{GS} , I _D =250μA
*G _{FS}	-	22.4	-	S	V _{DS} = 10V, I _D =10A
I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
I _{DSS}	-	-	1	μA	V _{DS} = 32V, V _{GS} = 0V
	-	-	10		V _{DS} = 32V, V _{GS} = 0V, T _j =85°C
*R _{DS(ON)}	-	2.8	3.7	mΩ	V _{GS} = 10V, I _D =20A
Dynamic					
*Q _g	-	73.8	110	nC	V _{DD} =20V, I _D =20A, V _{GS} =10V
*Q _{gs}	-	17.3	35		
*Q _{gd}	-	19.4	39		
*t _{d(ON)}	-	27.8	-	ns	V _{DD} =20V, I _D =20A, V _{GS} =10V, R _G =2.7Ω
*t _r	-	10.8	-		
*t _{d(OFF)}	-	57	-		
*t _f	-	13	-		
C _{iss}	-	4044	5258	pF	V _{GS} =0V, V _{DS} =25V, f=1MHz
C _{oss}	-	568	738		
C _{rss}	-	330	429		
R _g	-	1.1	-	Ω	f=1MHz
Source-Drain Diode					
*I _S	-	-	86	A	
*V _{SD}	-	0.79	1.2	V	I _S =20A, V _{GS} =0V
*t _{rr}	-	23.1	-	ns	V _{GS} =0, I _F =20A, dI _F /dt=100A/μs
*Q _{rr}	-	15.0	-	nC	

*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

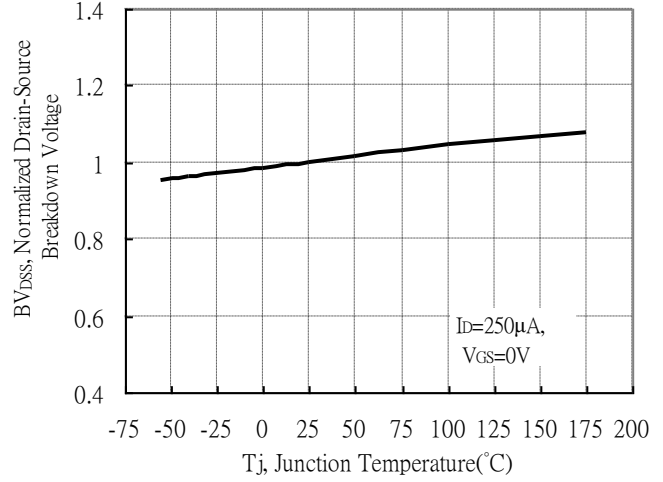
Recommended soldering footprint

 Unit ($\frac{\text{mm}}{\text{inch}}$)

Typical Characteristics

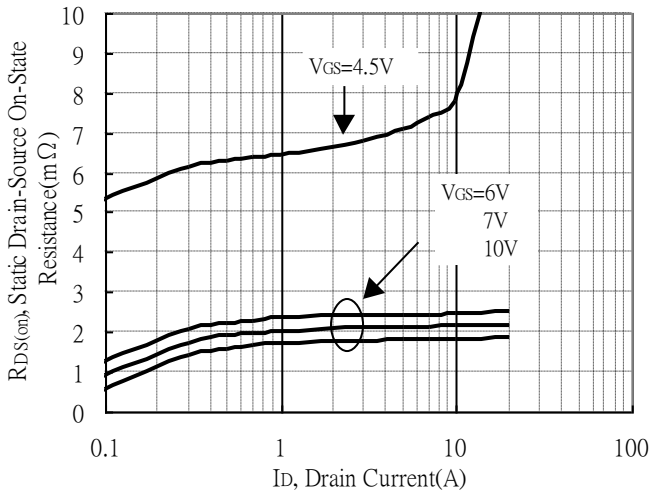
Typical Output Characteristics



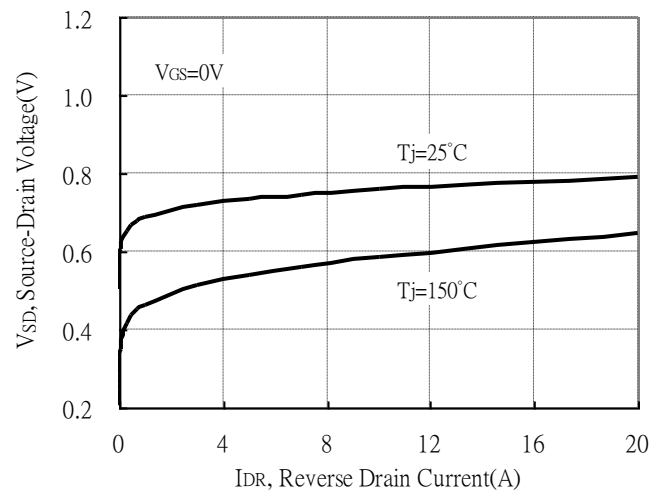
Brekdown Voltage vs Ambient Temperature



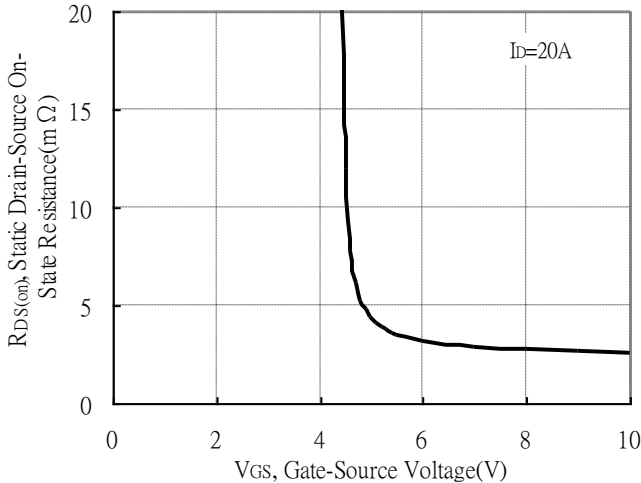
Static Drain-Source On-State resistance vs Drain Current



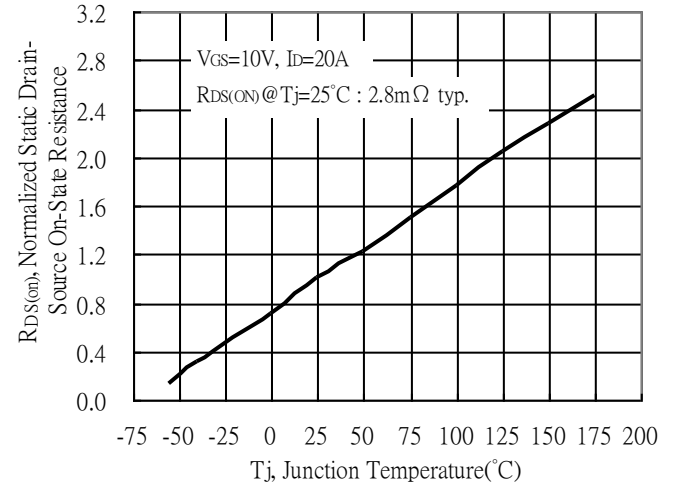
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

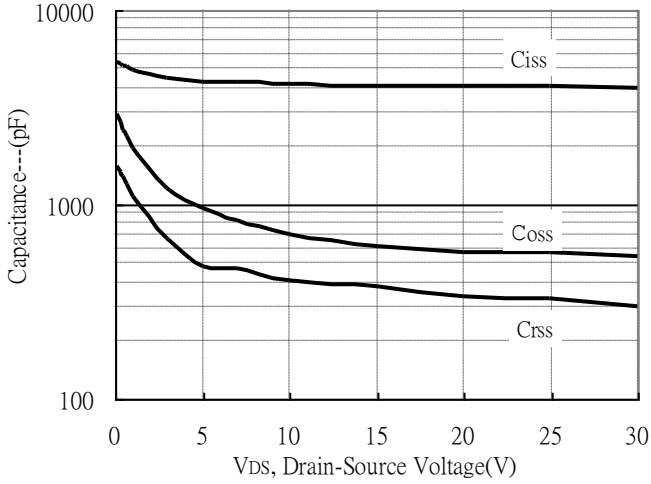


Drain-Source On-State Resistance vs Junction Temperature

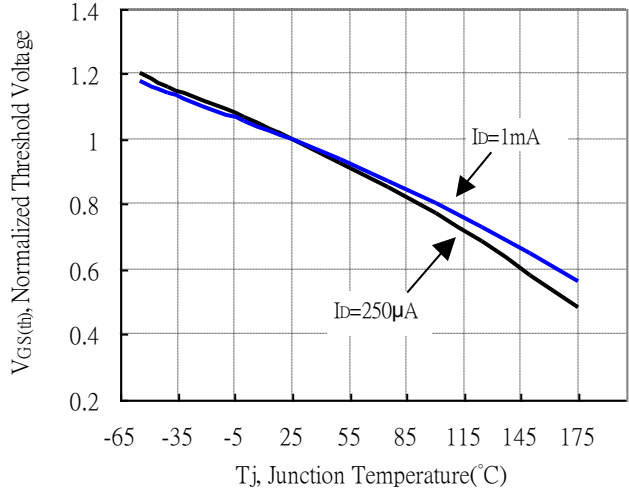


Typical Characteristics(Cont.)

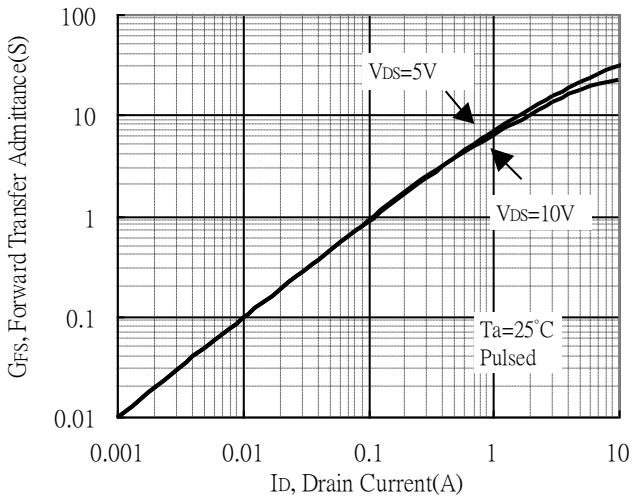
Capacitance vs Drain-to-Source Voltage



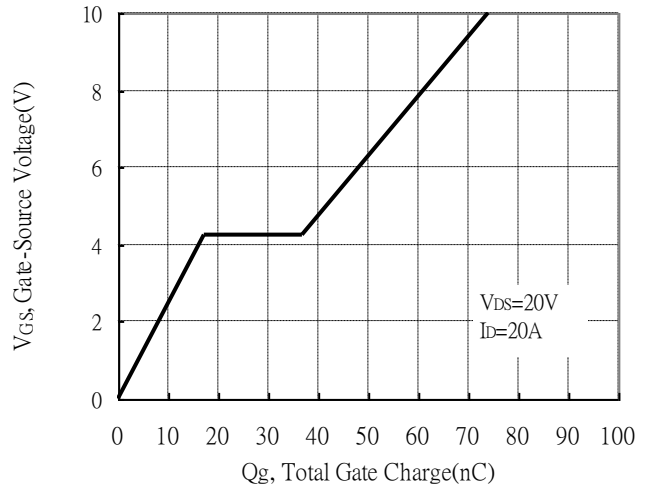
Threshold Voltage vs Junction Temperature



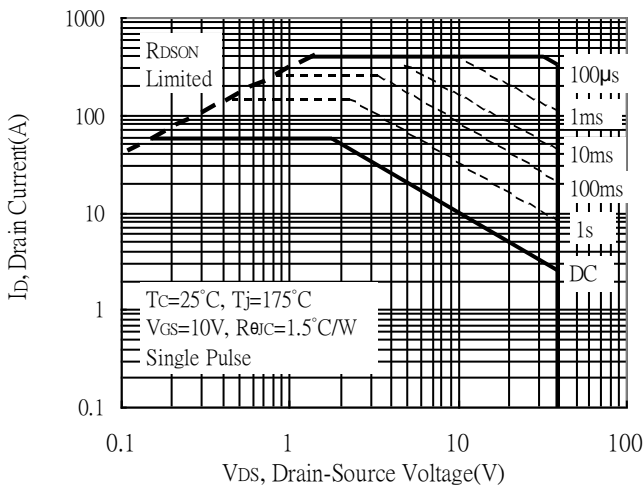
Forward Transfer Admittance vs Drain Current



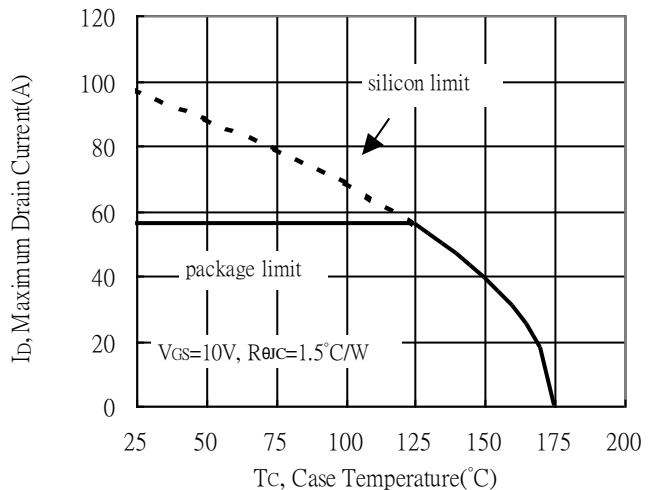
Gate Charge Characteristics



Maximum Safe Operating Area



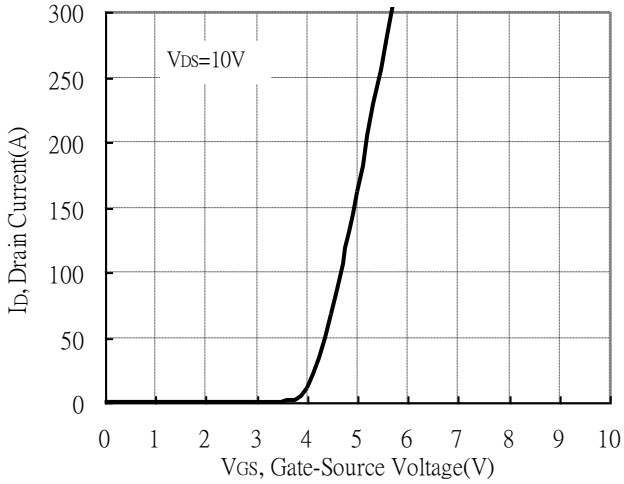
Maximum Drain Current vs Case Temperature



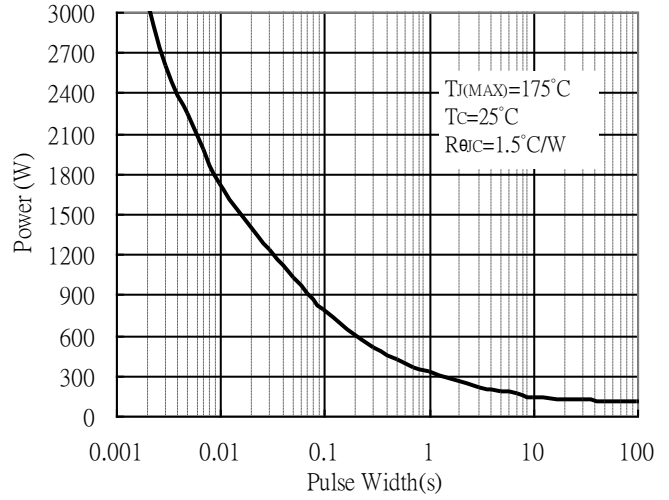


Typical Characteristics(Cont.)

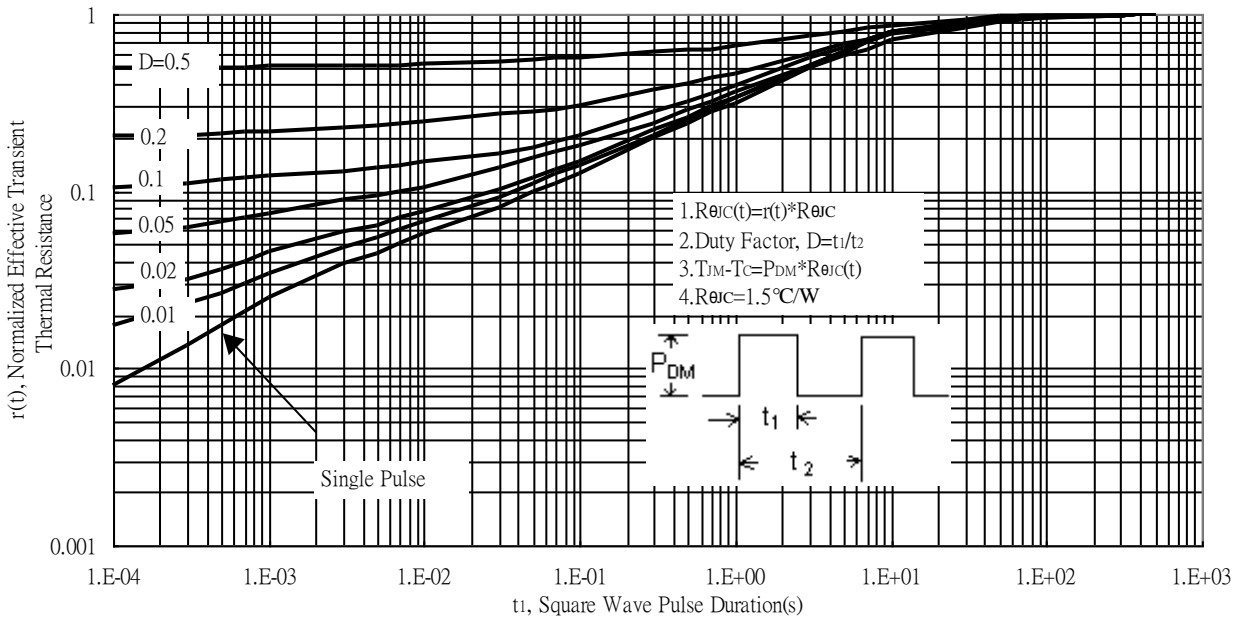
Typical Transfer Characteristics



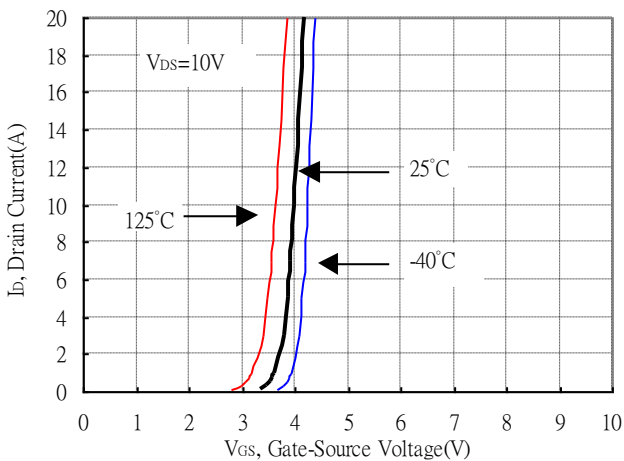
Single Pulse Power Rating, Junction to Case



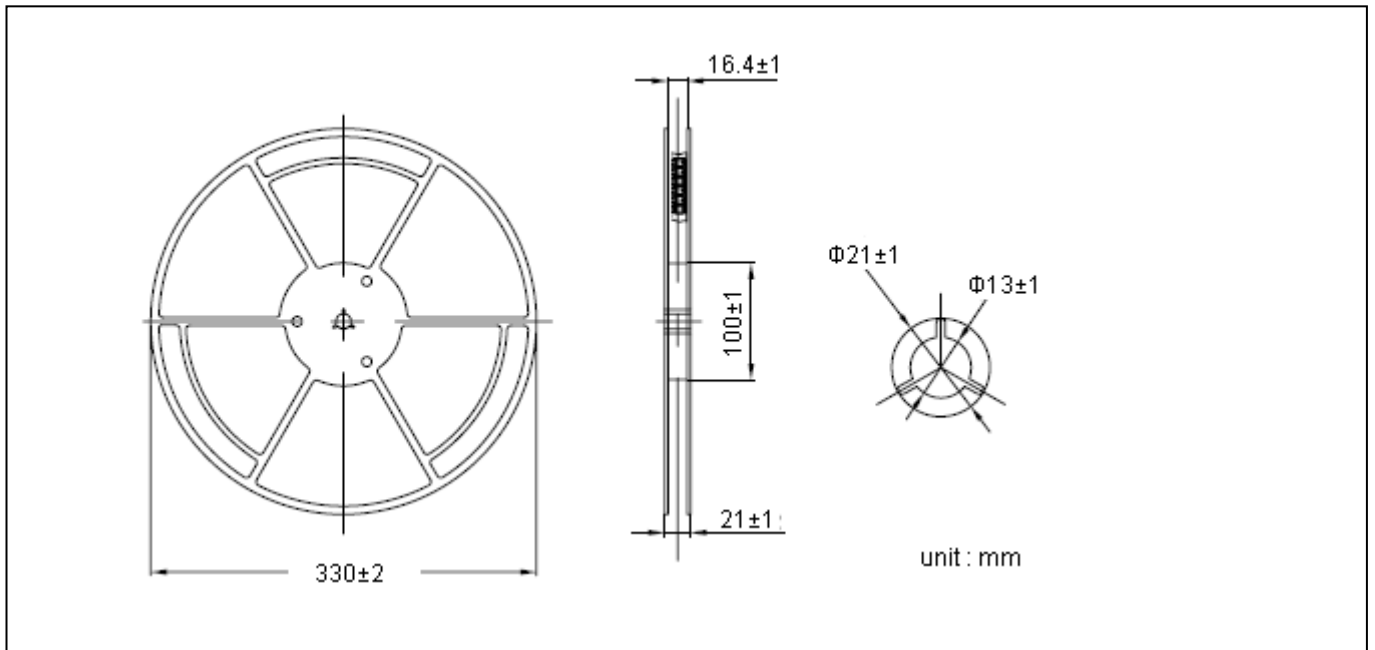
Transient Thermal Response Curves



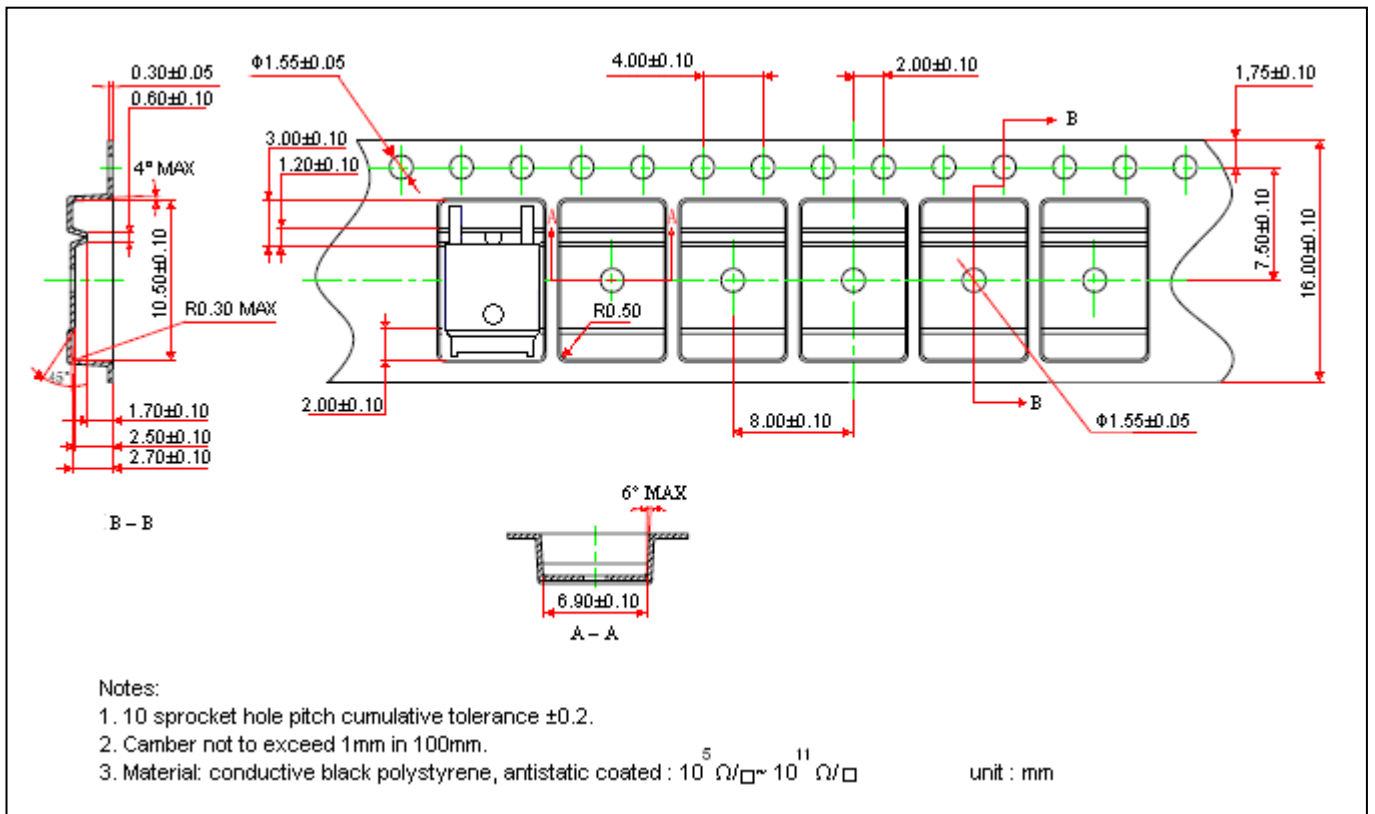
Typical Transfer Characteristics



Reel Dimension



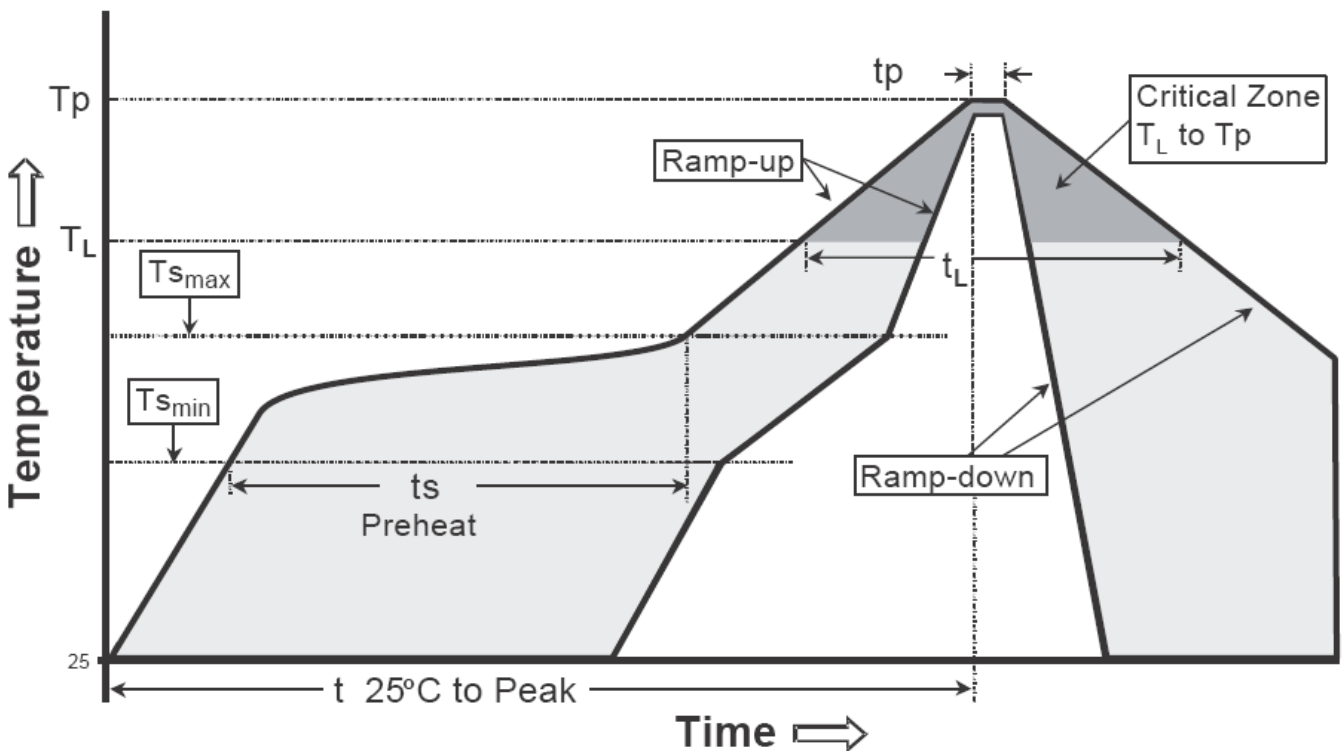
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

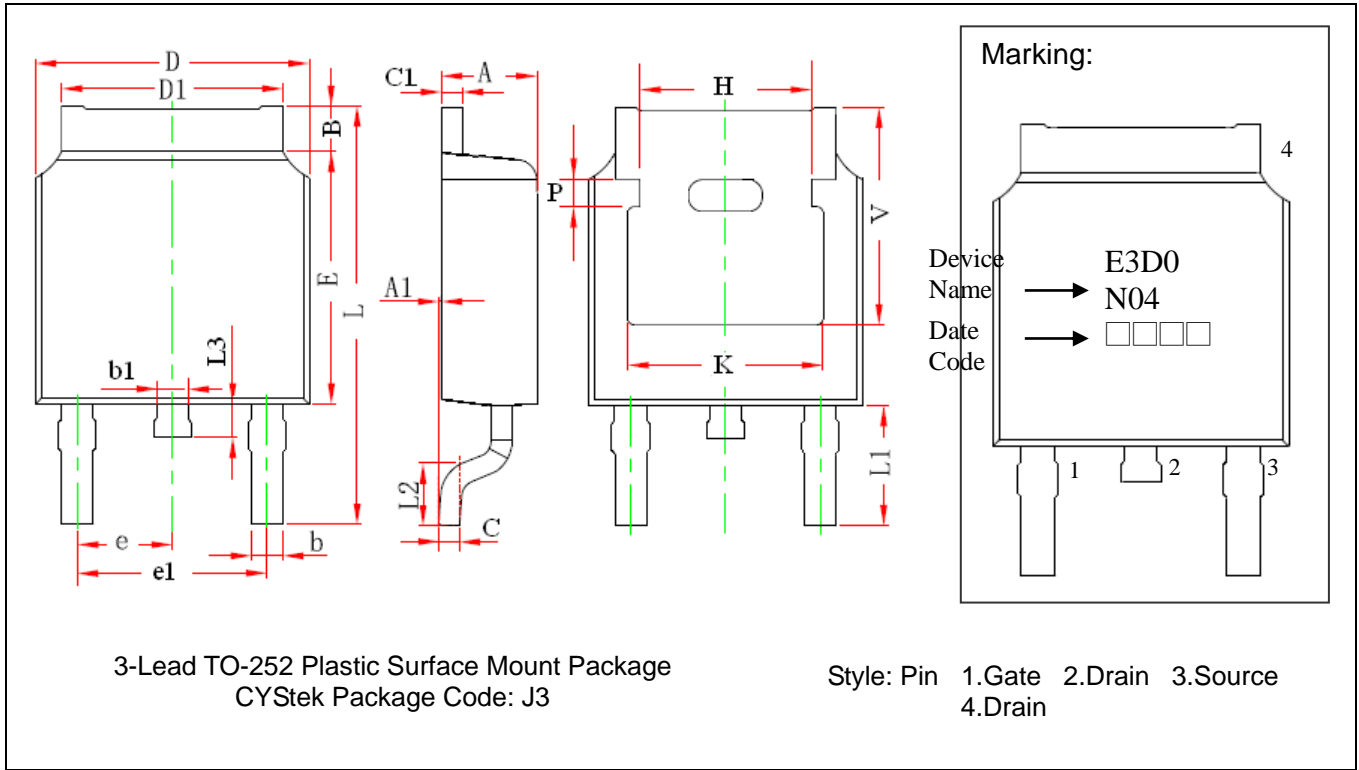
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _p)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-252 Dimension



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	e	0.086	0.094	2.186	2.386
A1	0.000	0.005	0.000	0.127	e1	0.172	0.188	4.372	4.772
B	0.039	0.048	0.990	1.210	H	0.163	REF	4.140	REF
b	0.026	0.034	0.660	0.860	K	0.190	REF	4.830	REF
b1	0.026	0.034	0.660	0.860	L	0.386	0.409	9.800	10.400
C	0.018	0.023	0.460	0.580	L1	0.114	REF	2.900	REF
C1	0.018	0.023	0.460	0.580	L2	0.055	0.067	1.400	1.700
D	0.256	0.264	6.500	6.700	L3	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	P	0.026	REF	0.650	REF
E	0.236	0.244	6.000	6.200	V	0.211	REF	5.350	REF

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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